Evy Eartice Semiconductor Corporation - <u>LCMXO3L-6900C-5BG324C Datasheet</u>



Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	858
Number of Logic Elements/Cells	6864
Total RAM Bits	245760
Number of I/O	279
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-LFBGA
Supplier Device Package	324-CABGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3I-6900c-5bg324c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



MachXO3 Family Data Sheet Introduction

January 2016

Features

Solutions

- Smallest footprint, lowest power, high data throughput bridging solutions for mobile applications
- Optimized footprint, logic density, IO count, IO performance devices for IO management and logic applications
- High IO/logic, lowest cost/IO, high IO devices for IO expansion applications

■ Flexible Architecture

- Logic Density ranging from 640 to 9.4K LUT4
- High IO to LUT ratio with up to 384 IO pins

Advanced Packaging

- 0.4 mm pitch: 1K to 4K densities in very small footprint WLCSP (2.5 mm x 2.5 mm to 3.8 mm x 3.8 mm) with 28 to 63 IOs
- 0.5 mm pitch: 640 to 6.9K LUT densities in 6 mm x 6 mm to 10 mm x 10 mm BGA packages with up to 281 IOs
- 0.8 mm pitch: 1K to 9.4K densities with up to 384 IOs in BGA packages

Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRx2, DDRx4

High Performance, Flexible I/O Buffer

- Programmable sysIO[™] buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8/1.5/1.2
 - LVTTL
 - LVDS, Bus-LVDS, MLVDS, LVPECL
 - MIPI D-PHY Emulated
 - Schmitt trigger inputs, up to 0.5 V hysteresis
- Ideal for IO bridging applications
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

■ Flexible On-Chip Clocking

- · Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
 - Wide input frequency range (7 MHz to 400 MHz)
- Non-volatile, Multi-time Programmable
 - Instant-on
 - Powers up in microseconds
 - · Optional dual boot with external SPI memory
 - Single-chip, secure solution
 - Programmable through JTAG, SPI or I²C
 - MachXO3L includes multi-time programmable NVCM
 - MachXO3LF infinitely reconfigurable Flash

 Supports background programming of non-volatile memory

TransFR Reconfiguration

In-field logic update while IO holds the system state

Enhanced System Level Support

- On-chip hardened functions: SPI, I²C, timer/ counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

Applications

- Consumer Electronics
- Compute and Storage
- Wireless Communications
- Industrial Control Systems
- Automotive System

Low Cost Migration Path

- Migration from the Flash based MachXO3LF to the NVCM based MachXO3L
- · Pin compatible and equivalent timing

© 2016 Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.

Advance Data Sheet DS1047



Table 1-1. MachXO3L/LF Family Selection Guide

Features		MachXO3L-640/ MachXO3LF-640	MachXO3L-1300/ MachXO3LF-1300	MachXO3L-2100/ MachXO3LF-2100	MachXO3L-4300/ MachXO3LF-4300	MachXO3L-6900/ MachXO3LF-6900	MachXO3L-9400/ MachXO3LF-9400
LUTs		640	1300	2100	4300	6900	9400
Distributed R/	AM (kbits)	5	10	16	34	54	73
EBR SRAM (I	kbits)	64	64	74	92	240	432
Number of PL	Ls	1	1	1	2	2	2
Hardened	l ² C	2	2	2	2	2	2
Functions:	SPI	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1
	Oscillator	1	1	1	1	1	1
MIPI D-PHY S	Support	Yes	Yes	Yes	Yes	Yes	Yes
Multi Time Pr NVCM	ogrammable	MachXO3L-640	MachXO3L-1300	MachXO3L-2100	MachXO3L-4300	MachXO3L-6900	MachXO3L-9400
Programmabl	e Flash	MachXO3LF-640	MachXO3LF-1300	MachXO3LF-2100	MachXO3LF-4300	MachXO3LF-6900	MachXO3LF-9400
Packages				ΙΟ			
36-ball WLCS (2.5 mm x 2.5	6P ¹ 6 mm, 0.4 mm)		28				
49-ball WLCS (3.2 mm x 3.2	P ¹ mm, 0.4 mm)			38			
81-ball WLCS (3.8 mm x 3.8	P ¹ mm, 0.4 mm)				63		
121-ball csfB0 (6 mm x 6 mm	GA ¹ n, 0.5 mm)	100	100	100	100		
256-ball csfB (9 mm x 9 mn	GA ¹ n, 0.5 mm)		206	206	206	206	206
324-ball csfB (10 mm x 10	GA ¹ mm, 0.5 mm)		2	268	268	281	
256-ball caBC (14 mm x 14 i	àA² mm, 0.8 mm)		206	206	206	206	206
324-ball caBC (15 mm x 15 i	àA² mm, 0.8 mm)			279	279	279	
400-ball caB0 (17 mm x 17 i	àA² mm, 0.8 mm)				335	335	335
484-ball caBC (19 mm x 19	3A² mm, 0.8 mm)						384

1. Package is only available for E=1.2 V devices.

2. Package is only available for C=2.5 V/3.3 V devices.

Introduction

MachXO3[™] device family is an Ultra-Low Density family that supports the most advanced programmable bridging and IO expansion. It has the breakthrough IO density and the lowest cost per IO. The device IO features have the integrated support for latest industry standard IO.

The MachXO3L/LF family of low power, instant-on, non-volatile PLDs has five devices with densities ranging from 640 to 9400 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I²C controller and timer/counter. MachXO3LF devices also support User Flash Memory (UFM). These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO3L/LF devices are designed on a 65nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs



Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE ¹	Output Clock Enable	Active High
RST	Reset	Active High
BE ¹	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	_
DI	Data In	_
DO	Data Out	_
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	_
FF	FIFO RAM Full Flag	_
AEF	FIFO RAM Almost Empty Flag	_
EF	FIFO RAM Empty Flag	_
RPRST	FIFO RAM Read Pointer Reset	_

Table 2-6. EBR Signal Descriptions

1. Optional signals.

2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.

3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.

4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).

In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port clock, CSR is the read port clock.

The EBR memory supports three forms of write behavior for single or dual port operation:

- 1. **Normal** Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
- 3. Read-Before-Write When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2 ^N -1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset



state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset



For further information on the sysMEM EBR block, please refer to TN1290, Memory Usage Guide for MachXO3 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram

Reset	
Clock	
Clock	

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f_{MAX} (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.



PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Pin Name	I/О Туре	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.



Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDRX4 (8:1) gearbox or as two ODDRX2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDRX4(8:1): D[7:0]		
GDDRX2(4:1)(IOL-A): D[3:0]		
GDDRX2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.



sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO3L/LF devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) input buffers are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO} .

MachXO3L/LF devices contain three types of sysIO buffer pairs.

1. Left and Right sysIO Buffer Pairs

The sysIO buffer pairs in the left and right banks of the device consist of two single-ended output drivers and two single-ended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the left and right of the devices also have differential input buffers.

2. Bottom sysIO Buffer Pairs

The sysIO buffer pairs in the bottom bank of the device consist of two single-ended output drivers and two single-ended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the bottom also have differential input buffers. Only the I/Os on the bottom banks have programmable PCI clamps and differential input termination. The PCI clamp is enabled after V_{CC} and V_{CCIO} are at valid operating levels and the device has been configured.

3. Top sysIO Buffer Pairs

The sysIO buffer pairs in the top bank of the device consist of two single-ended output drivers and two singleended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the top also have differential I/O buffers. Half of the sysIO buffer pairs on the top edge have true differential outputs. The sysIO buffer pair comprising of the A and B PIOs in every PIC on the top edge have a differential output driver.

Typical I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC} and V_{CCIO0} have reached V_{PORUP} level defined in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. The default configuration of the I/O pins in a blank device is tri-state with a weak pulldown to GND (some pins such as PROGRAMN and the JTAG pins have weak pull-up to V_{CCIO} as the default functionality). The I/O pins will maintain the blank configuration until V_{CC} and V_{CCIO} (for I/O banks containing configuration I/Os) have reached V_{PORUP} levels at which time the I/Os will take on the user-configured settings only after a proper download/configuration.

There are various ways a user can ensure that there are no spurious signals on critical outputs as the device powers up. These are discussed in more detail in TN1280, MachXO3 sysIO Usage Guide.

Supported Standards

The MachXO3L/LF sysIO buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL, and PCI. The buffer supports the LVTTL, PCI, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individually configurable options for drive strength, bus maintenance (weak pull-up, weak pull-down, bus-keeper latch or none) and open drain. BLVDS, MLVDS and LVPECL output emulation is supported on all devices. The MachXO3L/LF devices support on-chip LVDS output buffers on approximately 50% of the I/Os on the top bank. Differential receivers for LVDS, BLVDS, MLVDS and LVPECL are supported on all banks of MachXO3L/LF devices. PCI support is provided in the bottom bank of the MachXO3L/LF devices. Table 2-11 summarizes the I/O characteristics of the MachXO3L/LF PLDs.



Table 2-17. MachXO3L/LF Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Differential I/O buffers (used to implement standards such as LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1289, Power Estimation and Management for MachXO3 Devices.

Power On Reset

MachXO3L/LF devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO} (controls configuration) voltage levels. It then triggers download from the on-chip configuration NVCM/Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For "E" devices without voltage regulators, V_{CCINT} is the same as the V_{CC} supply voltage. For "C" devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as NVCM/Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration. Note that for "C" devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once an "E" device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a mini-mal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.



MachXO3 Family Data Sheet DC and Switching Characteristics

February 2017

Advance Data Sheet DS1047

Absolute Maximum Ratings^{1, 2, 3}

	MachXO3L/LF E (1.2 V)	MachXO3L/LF C (2.5 V/3.3 V)
Supply Voltage V _{CC}	\ldots .–0.5 V to 1.32 V \ldots .	–0.5 V to 3.75 V
Output Supply Voltage V _{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied ^{4, 5}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied ⁴	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T ₁)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

5. The dual function I^2C pins SCL and SDA are limited to -0.25 V to 3.75 V or to -0.3 V with a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
Vaa ¹	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
VCC	Core Supply Voltage for 2.5 V/3.3 V Devices	2.375	3.465	V
V _{CCIO} ^{1, 2, 3}	I/O Driver Supply Voltage	1.14	3.465	V
t _{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature Industrial Operation	-40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates¹

	iyp.	wax.	Units
t _{RAMP} Power supply ramp rates for all power supplies. 0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

^{© 2017} Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.



Programming and Erase Supply Current – C/E Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ.⁴	Units
I _{CC}	Core Power Supply	LCMXO3L/LF-1300C 256 Ball Package	22.1	mA
		LCMXO3L/LF-2100C	22.1	mA
		LCMXO3L/LF-2100C 324 Ball Package	26.8	mA
		LCMXO3L/LF-4300C	26.8	mA
		LCMXO3L/LF-4300C 400 Ball Package	33.2	mA
		LCMXO3L/LF-6900C	33.2	mA
		LCMXO3L/LF-9400C	39.6	mA
		LCMXO3L/LF-640E	17.7	mA
		LCMXO3L/LF-1300E	17.7	mA
		LCMXO3L/LF-1300E 256 Ball Package	18.3	mA
		LCMXO3L/LF-2100E	18.3	mA
		LCMXO3L/LF-2100E 324 Ball Package	20.4	mA
		LCMXO3L/LF-4300E	20.4	mA
		LCMXO3L/LF-6900E	23.9	mA
		LCMXO3L/LF-9400E	28.5	mA
I _{CCIO}	Bank Power Supply ⁵ VCCIO = 2.5 V	All devices	0	mA

1. For further information on supply current, please refer to TN1289, Power Estimation and Management for MachXO3 Devices.

2. Assumes all inputs are held at $V_{\mbox{\scriptsize CCIO}}$ or GND and all outputs are tri-stated.

3. Typical user pattern.

4. JTAG programming is at 25 MHz.

5. $T_J = 25$ °C, power supplies at nominal voltage.

6. Per bank. $V_{CCIO} = 2.5$ V. Does not include pull-up/pull-down.



MIPI D-PHY Emulation

MachXO3L/LF devices can support MIPI D-PHY unidirectional HS (High Speed) and bidirectional LP (Low Power) inputs and outputs via emulation. In conjunction with external resistors High Speed IOs use the LVDS25E buffer and Low Power IOs use the LVCMOS buffers. The scheme shown in Figure 3-4 is one possible solution for MIPI D-PHY Receiver implementation. The scheme shown in Figure 3-5 is one possible solution for MIPI D-PHY Transmitter implementation.

Figure 3-4. MIPI D-PHY Input Using External Resistors



Table 3-4. MIPI DC Conditions¹

	Description	Min.	Тур.	Max.	Units			
Receiver								
External Terminatio	n							
RT	1% external resistor with VCCIO=2.5 V		50	—	Ohms			
	1% external resistor with VCCIO=3.3 V	—	50	—	Ohms			
High Speed								
VCCIO	VCCIO of the Bank with LVDS Emulated input buffer	—	2.5	—	V			
	VCCIO of the Bank with LVDS Emulated input buffer	—	3.3	—	V			
VCMRX	Common-mode voltage HS receive mode	150	200	250	mV			
VIDTH	Differential input high threshold	—	—	100	mV			
VIDTL	Differential input low threshold	-100	—	—	mV			
VIHHS	Single-ended input high voltage		—	300	mV			
VILHS	Single-ended input low voltage	100	—	—	mV			
ZID	Differential input impedance	80	100	120	Ohms			



DC and Switching Characteristics MachXO3 Family Data Sheet

			-6		-5		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Units
		MachXO3L/LF-1300	2.87		3.18		ns
		MachXO3L/LF-2100	2.87		3.18	—	ns
t _{SU_DELPLL}	Clock to Data Setup - PIO Input Register	MachXO3L/LF-4300	2.96		3.28		ns
	inin Bata inpat Bolay	MachXO3L/LF-6900	3.05		3.35		ns
		MachXO3L/LF-9400	3.06		3.37		ns
		MachXO3L/LF-1300	-0.83		-0.83		ns
		MachXO3L/LF-2100	-0.83		-0.83		ns
t _{H DELPLL}	Clock to Data Hold - PIO Input Register with	MachXO3L/LF-4300	-0.87		-0.87		ns
		MachXO3L/LF-6900	-0.91		-0.91	—	ns
		MachXO3L/LF-9400	-0.93	—	-0.93		ns



			-	6	-	-5	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Units
Generic DDF GDDRX1_RX	RX1 Inputs with Clock and Data Aligned at K.SCLK.Aligned ^{8,9}	Pin Using PCLK Pin for Clo	ock Inpu	t –		1	
t _{DVA}	Input Data Valid After CLK			0.317	—	0.344	UI
t _{DVE}	Input Data Hold After CLK	All MachXO3L/LF	0.742		0.702		UI
f _{DATA}	DDRX1 Input Data Speed	-devices, all sides		300	—	250	Mbps
f _{DDRX1}	DDRX1 SCLK Frequency			150	—	125	MHz
Generic DD GDDRX1_R	RX1 Inputs with Clock and Data Centered X.SCLK.Centered ^{8, 9}	at Pin Using PCLK Pin fo	or Clock	Input –		1	1
t _{SU}	Input Data Setup Before CLK		0.566		0.560		ns
t _{HO}	Input Data Hold After CLK	All MachXO3L/LF	0.778		0.879		ns
f _{DATA}	DDRX1 Input Data Speed	-devices, all sides		300	—		Mbps
f _{DDRX1}	DDRX1 SCLK Frequency		_	150	—	125	MHz
Generic DD GDDRX2_R	RX2 Inputs with Clock and Data Aligned at X.ECLK.Aligned ^{8, 9}	Pin Using PCLK Pin for C	lock Inp	but –			
t _{DVA}	Input Data Valid After CLK		—	0.316	—	0.342	UI
t _{DVE}	Input Data Hold After CLK	-	0.710		0.675		UI
f _{DATA}	DDRX2 Serial Input Data Speed	MachXO3L/LF devices,		664	—	554	Mbps
f _{DDRX2}	DDRX2 ECLK Frequency	bottom side only		332	—	277	MHz
f _{SCLK}	SCLK Frequency			166	—	139	MHz
Generic DDRX2 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input –							
t _{SU}	Input Data Setup Before CLK		0.233		0.219		ns
t _{HO}	Input Data Hold After CLK	-	0.287	—	0.287		ns
f _{DATA}	DDRX2 Serial Input Data Speed	MachXO3L/LF devices,		664	—	554	Mbps
f _{DDRX2}	DDRX2 ECLK Frequency	bottom side only		332	—	277	MHz
f _{SCLK}	SCLK Frequency	-		166	—	139	MHz
Generic DDI	R4 Inputs with Clock and Data Aligned at P	in Using PCLK Pin for Cloo	k Input	- GDDR	X4_RX.	ECLK.A	ligned ⁸
t _{DVA}	Input Data Valid After ECLK		—	0.307	—	0.320	UI
t _{DVE}	Input Data Hold After ECLK	-	0.782	—	0.699	—	UI
f _{DATA}	DDRX4 Serial Input Data Speed	MachXO3L/LF devices,		800	—	630	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency	bottom side only		400	—	315	MHz
f _{SCLK}	SCLK Frequency			100	—	79	MHz
Generic DDF	A4 Inputs with Clock and Data Centered at P	in Using PCLK Pin for Cloc	k Input	- GDDR	X4_RX.E	CLK.Ce	entered ⁸
t _{SU}	Input Data Setup Before ECLK		0.233	—	0.219	—	ns
t _{HO}	Input Data Hold After ECLK		0.287	—	0.287		ns
f _{DATA}	DDRX4 Serial Input Data Speed	MachXO3L/LF devices,	_	800	—	630	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency		_	400	—	315	MHz
f _{SCLK}	SCLK Frequency			100	—	79	MHz
7:1 LVDS In	outs (GDDR71_RX.ECLK.7:1) ⁹						
t _{DVA}	Input Data Valid After ECLK		—	0.290	—	0.320	UI
t _{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	UI
f _{DATA}	DDR71 Serial Input Data Speed	MachXO3L/LF devices,	—	756	—	630	Mbps
f _{DDR71}	DDR71 ECLK Frequency	bottom side only	—	378	—	315	MHz
f _{CLKIN}	7:1 Input Clock Frequency (SCLK) (mini- mum limited by PLL)		_	108	—	90	MHz



sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min.	Max.	Units
f _{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f _{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS)		1.5625	400	MHz
f _{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f _{VCO}	PLL VCO Frequency		200	800	MHz
f _{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteri	stics	·			
t _{DT}	Output Clock Duty Cycle	Without duty trim selected ³	45	55	%
t _{DT_TRIM} ⁷	Edge Duty Trim Accuracy		-75	75	%
t _{PH} ⁴	Output Phase Accuracy		-6	6	%
	Output Cleak Pariad littar	f _{OUT} > 100 MHz	—	150	ps p-p
		f _{OUT} < 100 MHz	—	0.007	UIPP
		f _{OUT} > 100 MHz	—	180	ps p-p
		f _{OUT} < 100 MHz	—	0.009	UIPP
+ 1.8	Output Clask Dhase litter	f _{PFD} > 100 MHz	—	160	ps p-p
^t OPJIT ¹¹	Output Clock Phase Jitter	f _{PFD} < 100 MHz	—	0.011	UIPP
	Output Clock Pariod litter (Fractional N)	f _{OUT} > 100 MHz	—	230	ps p-p
	Output Clock Period Jitter (Fractional-N)	f _{OUT} < 100 MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter	f _{OUT} > 100 MHz	—	230	ps p-p
	(Fractional-N)	f _{OUT} < 100 MHz	—	0.12	UIPP
t _{SPO}	Static Phase Offset	Divider ratio = integer	-120	120	ps
t _W	Output Clock Pulse Width	At 90% or 10% ³	0.9	—	ns
tLOCK ^{2, 5}	PLL Lock-in Time		—	15	ms
t _{UNLOCK}	PLL Unlock Time		—	50	ns
• 6	Innut Cleak Davied Litter	f _{PFD} ≥ 20 MHz	—	1,000	ps p-p
'IPJIT		f _{PFD} < 20 MHz	—	0.02	UIPP
t _{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t _{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t _{STABLE} ⁵	STANDBY High to PLL Stable		—	15	ms
t _{RST}	RST/RESETM Pulse Width		1	_	ns
t _{RSTREC}	RST Recovery Time		1		ns
t _{RST DIV}	RESETC/D Pulse Width		10		ns
t _{RSTREC} DIV	RESETC/D Recovery Time		1		ns
t _{ROTATE-SETUP}	PHASESTEP Setup Time		10		ns
t _{ROTATE_WD}	PHASESTEP Pulse Width		4	—	VCO Cycles

Over Recommended Operating Conditions

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.

2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.

3. Using LVDS output buffers.

4. CLKOS as compared to CLKOP output for one phase step at the maximum VCO frequency. See TN1282, MachXO3 sysCLOCK PLL Design and Usage Guide for more details.

5. At minimum $\rm f_{PFD}$ As the $\rm f_{PFD}$ increases the time will decrease to approximately 60% the value listed.

6. Maximum allowed jitter on an input clock. PLL unlock may occur if the input jitter exceeds this specification. Jitter on the input clock may be transferred to the output clocks, resulting in jitter measurements outside the output specifications listed in this table.

7. Edge Duty Trim Accuracy is a percentage of the setting value. Settings available are 70 ps, 140 ps, and 280 ps in addition to the default value of none.

8. Jitter values measured with the internal oscillator operating. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.



JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f _{MAX}	TCK clock frequency	—	25	MHz
t _{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t _{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t _{BTS}	TCK [BSCAN] setup time	10	—	ns
t _{BTH}	TCK [BSCAN] hold time	8	—	ns
t _{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
t _{BTCODIS}	TAP controller falling edge of clock to valid disable	—	10	ns
t _{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t _{BTCRS}	BSCAN test capture register setup time	8	—	ns
t _{BTCRH}	BSCAN test capture register hold time	20	—	ns
t _{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
t _{BTUODIS}	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
t _{BTUPOEN}	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-8. JTAG Port Timing Waveforms





I²C Port Timing Specifications^{1, 2}

Symbol	Parameter	Min.	Max.	Units
f _{MAX}	Maximum SCL clock frequency		400	kHz

1. MachXO3L/LF supports the following modes:

• Standard-mode (Sm), with a bit rate up to 100 kbit/s (user and configuration mode)

• Fast-mode (Fm), with a bit rate up to 400 kbit/s (user and configuration mode)

2. Refer to the I^2C specification for timing requirements.

SPI Port Timing Specifications¹

Symbol	Parameter	Min.	Max.	Units
f _{MAX}	Maximum SCK clock frequency		45	MHz

1. Applies to user mode only. For configuration mode timing specifications, refer to sysCONFIG Port Timing Specifications table in this data sheet.

Switching Test Conditions

Figure 3-9 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-9. Output Test Load, LVTTL and LVCMOS Standards



Table 3-6. Test Fixture Required Components	, Non-Terminated Interfaces
---	-----------------------------

Test Condition	R1	CL	Timing Ref.	VT
			LVTTL, LVCMOS 3.3 = 1.5 V	_
		0pF	LVCMOS 2.5 = $V_{CCIO}/2$	_
LVTTL and LVCMOS settings (L -> H, H -> L)	∞		LVCMOS 1.8 = $V_{CCIO}/2$	
			LVCMOS 1.5 = $V_{CCIO}/2$	_
			LVCMOS 1.2 = $V_{CCIO}/2$	_
LVTTL and LVCMOS 3.3 (Z -> H)			1.5	V _{OL}
LVTTL and LVCMOS 3.3 (Z -> L)			1.5	V _{OH}
Other LVCMOS (Z -> H)	188	0nE	V _{CCIO} /2	V _{OL}
Other LVCMOS (Z -> L)	100	орі	V _{CCIO} /2	V _{OH}
LVTTL + LVCMOS (H -> Z)			V _{OH} - 0.15	V _{OL}
LVTTL + LVCMOS (L -> Z)			V _{OL} - 0.15	V _{OH}

Note: Output test conditions for all other interfaces are determined by the respective standards.



	MachXO3L/LF-2100					
	WLCSP49	CSFBGA121	CSFBGA256	CSFBGA324	CABGA256	CABGA324
General Purpose IO per Bank		•	•			
Bank 0	19	24	50	71	50	71
Bank 1	0	26	52	62	52	68
Bank 2	13	26	52	72	52	72
Bank 3	0	7	16	22	16	24
Bank 4	0	7	16	14	16	16
Bank 5	6	10	20	27	20	28
Total General Purpose Single Ended IO	38	100	206	268	206	279
Differential IO per Bank						
Bank 0	10	12	25	36	25	36
Bank 1	0	13	26	30	26	34
Bank 2	6	13	26	36	26	36
Bank 3	0	3	8	10	8	12
Bank 4	0	3	8	6	8	8
Bank 5	3	5	10	13	10	14
Total General Purpose Differential IO	19	49	103	131	103	140
Dual Function IO	25	33	33	37	33	37
Number 7:1 or 8:1 Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	7	14	18	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	13	14	18	14	18
High-speed Differential Outputs						
Bank 0	5	7	14	18	14	18
VCCIO Pins		•	•			
Bank 0	2	1	4	4	4	4
Bank 1	0	1	3	4	4	4
Bank 2	1	1	4	4	4	4
Bank 3	0	1	2	2	1	2
Bank 4	0	1	2	2	2	2
Bank 5	1	1	2	2	1	2
VCC	2	4	8	8	8	10
GND	4	10	24	16	24	16
NC	0	0	0	13	1	0
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	49	121	256	324	256	324



MachXO3 Family Data Sheet Ordering Information

May 2016

Advance Data Sheet DS1047

MachXO3 Part Number Description



Ordering Information

MachXO3L/LF devices have top-side markings as shown in the examples below, on the 256-Ball caBGA package with MachXO3-6900 device in Commercial Temperature in Speed Grade 5. Notice that for the MachXO3LF device, *LMXO3LF* is used instead of *LCMXO3LF* as in the Part Number.



with LMXO3LF

Note: Markings are abbreviated for small packages.

^{© 2016} Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.



MachXO3 Family Data Sheet Revision History

February 2017

Advance Data Sheet DS1047

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected "MDVS" to "MLDVS" in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected "t _{DVB} " to "t _{DIB} " and "t _{DVA} " to "t _{DIA} " and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF- 9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Volt- age Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V _{REF} (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.

^{© 2017} Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.



Date	Version	Section	Change Summary
September 2015	1.5	DC and Switching Characteristics	Updated the MIPI D-PHY Emulation section. Revised Table 3-5, MIPI D- PHY Output DC Conditions. — Revised RL Typ. value. — Revised RH description and values.
			Updated the Maximum sysIO Buffer Performance section. Revised MIPI Max. Speed value.
			Updated the MachXO3L/LF External Switching Characteristics – C/E Devices section. Added footnotes 14 and 15.
August 2015	1.4	Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.
		Ordering Information	Updated the top side markings section to indicate the use of LMXO3LF for the LCMXO3LF device.
March 2015	1.3	All	General update. Added MachXO3LF devices.
October 2014	1.2	Introduction	Updated Table 1-1, MachXO3L Family Selection Guide. Revised XO3L- 2100 and XO3L-4300 IO for 324-ball csfBGA package.
		Architecture	Updated the Dual Boot section. Corrected information on where the pri- mary bitstream and the golden image must reside.
		Pinout Information	Updated the Pin Information Summary section.
			Changed General Purpose IO Bank 5 values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package.
			Changed Number 7:1 or 8:1 Gearboxes for MachXO3L-640 and MachXO3L-1300.
			Removed DQS Groups (Bank 1) section.
			Changed VCCIO Pins Bank 1 values for MachXO3L-1300, MachXO3L- 2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package.
			Changed GND values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package.
			Changed NC values for MachXO3L-2100 and MachXO3L-4300 CSF- BGA 324 package.
		DC and Switching Characteristics	Updated the BLVDS section. Changed output impedance nominal values in Table 3-2, BLVDS DC Condition.
			Updated the LVPECL section. Changed output impedance nominal value in Table 3-3, LVPECL DC Condition.
			Updated the sysCONFIG Port Timing Specifications section. Updated INITN low time values.
July 2014	1.1	DC and Switching Characteristics	Updated the Static Supply Current – C/E Devices section. Added devices.
			Updated the Programming and Erase Supply Current – C/E Device section. Added devices.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Revised footnote 4.
			Added the NVCM Download Time section.
			Updated the Typical Building Block Function Performance – C/E Devices section. Added information to footnote.
		Pinout Information	Updated the Pin Information Summary section.
		Ordering Information	Updated the MachXO3L Part Number Description section. Added packages.
			Updated the Ordering Information section. General update.